

SOT-227 Power Module Single Switch - Silicon Carbide Power MOSFET 200 A



SOT-227

FEATURES

- High blocking voltage with low on-resistance
- High speed switching with low capacitance
- Soft body diode with low reverse recovery
- Maximum 175 °C junction temperature
- UL approved file E78996 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

APPLICATIONS

- EV chargers
- Server and telecom PSU
- UPS
- Solar Inverters
- SMPS
- DC/DC converters

PRIMARY CHARACTERISTICS

V_{DSS}	1200 V
$R_{DS(on)}$ at 200 A	12.1 mΩ
I_D	127 A at 90 °C
Type	SiC MOSFET Modules
Package	SOT-227

DESCRIPTION

This is an high performance silicon carbide MOSFET. The high blocking voltage with low on-resistance, high speed switching with low capacitance make this MOSFET ideal for high frequency switching application including solar inverters and EV chargers.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
MOSFET				
Drain to source voltage	V_{DSS}		1200	V
Continuous drain current, V_{GS} at 15 V	I_D	$T_C = 25\text{ °C}$	163	A
		$T_C = 90\text{ °C}$	127	
Pulsed drain current	$I_{DM}^{(1)}$		380	
Power dissipation	P_D	$T_C = 25\text{ °C}$	750	W
Gate to source voltage	V_{GS}		-8 / +19	V
MODULE				
Operating junction temperature range	T_J		-55 to +175	°C
Operating storage temperature range	T_{Stg}		-40 to +150	
Insulation voltage (RMS)	V_{ISOL}	any terminal to case, $t = 1\text{ min}$	2500	V

Note

⁽¹⁾ Limited at max. junction temperature

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	RATING	UNITS
Recommended operating gate - source voltage	$V_{GS(op)}$	-4 / +15	V

**THERMAL AND MECHANICAL SPECIFICATIONS**

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	T_J		-55	-	175	°C
Operating storage temperature range	T_{Stg}		-40	-	150	
Junction to case MOSFET	R_{thJC}		-	-	0.2	°C/W
Case to heatsink Module	R_{thCS}	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf. in)
		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf. in)
Case style			SOT-227			

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ °C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain to source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}$, $I_D = 400\text{ }\mu\text{A}$	1200	-	-	V
Breakdown voltage temperature coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	$I_D = 400\text{ }\mu\text{A}$ (25 °C to 125 °C)	-	0.45	-	mV/°C
Static drain to source on-resistance	$R_{DS(on)}$	$V_{GS} = 15\text{ V}$, $I_D = 200\text{ A}$	-	12.1	17.25	mΩ
		$V_{GS} = 15\text{ V}$, $I_D = 200\text{ A}$, $T_J = 175\text{ °C}$	-	2.2	-	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 28.44\text{ mA}$	1.7	2.6	3.7	V
		$V_{DS} = V_{GS}$, $I_D = 28.44\text{ mA}$, $T_J = 150\text{ °C}$	-	2.5	-	
Temperature coefficient of threshold voltage	$\Delta V_{GS(th)}/\Delta T_J$	$V_{DS} = V_{GS}$, $I_D = 28.44\text{ mA}$ (25 °C to 125 °C)	-	-2.6	-	mV/°C
Forward transconductance	g_{fs}	$V_{DS} = 20\text{ V}$, $I_D = 200\text{ A}$	-	111	-	S
Drain to source leakage current	I_{DSS}	$V_{DS} = 1200\text{ V}$, $V_{GS} = 0\text{ V}$	-	0.4	200	μA
		$V_{DS} = 1200\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 150\text{ °C}$	-	1.8	-	
Gate to source leakage	I_{GSS}	$V_{GS} = 15\text{ V}$	-	-	250	nA
Total gate charge	Q_g	$I_D = 100\text{ A}$, $V_{DS} = 800\text{ V}$, $V_{GS} = -4\text{ V} / +15\text{ V}$	-	331	-	nC
Gate to source charge	Q_{gs}		-	70	-	
Gate to drain ("Miller") charge	Q_{gd}		-	107	-	
Turn-on switching energy	E_{on}	$V_{DD} = 800\text{ V}$, $I_D = 200\text{ A}$, $R_g = 2.2\text{ }\Omega$, $V_{GS} = -4\text{ V} / +15\text{ V}$	-	3.291	-	mJ
Turn-off switching energy	E_{off}		-	3.205	-	
Turn-on delay time	$t_{d(on)}$		-	28.32	-	ns
Rise time	t_r		-	49.6	-	
Turn-off delay time	$t_{d(off)}$		-	52.48	-	
Fall time	t_f		-	14.08	-	
Turn-on switching energy	E_{on}	$V_{DD} = 800\text{ V}$, $I_D = 200\text{ A}$, $R_g = 2.2\text{ }\Omega$, $V_{GS} = -4\text{ V} / +15\text{ V}$, $T_J = 125\text{ °C}$	-	2.096	-	mJ
Turn-off switching energy	E_{off}		-	3.24	-	
Turn-on delay time	$t_{d(on)}$		-	27.68	-	ns
Rise time	t_r		-	36.32	-	
Turn-off delay time	$t_{d(off)}$		-	58.24	-	
Fall time	t_f		-	14.08	-	
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 1000\text{ V}$, $f = 100\text{ kHz}$	-	9123	-	pF
Output capacitance	C_{oss}		-	143	-	
Reverse transfer capacitance	C_{rss}		-	33	-	

SOURCE-DRAIN RATINGS AND CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Pulsed source current (body diode)	I_{SM}	10 ms sine or 6 ms rectangular pulse, $T_J = 175\text{ }^{\circ}\text{C}$	-	-	441	A
Diode forward voltage	V_{SD}	$I_S = 200\text{ A}$, $V_{GS} = 0\text{ V}$	-	5.71	6.0	V
Reverse recovery time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$, $I_F = I_S = 200\text{ A}$, $di/dt = 12\text{ }240\text{ A}/\mu\text{s}$, $V_R = 800\text{ V}$	-	17.28	-	ns
Reverse recovery charge	Q_{rr}		-	388	-	nC
Reverse recovery current	I_{RRM}		-	81	-	A

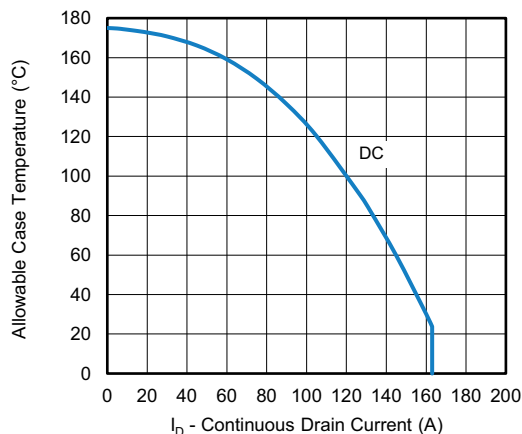


Fig. 1 - Max. Continuous Drain Current vs. Case Temperature

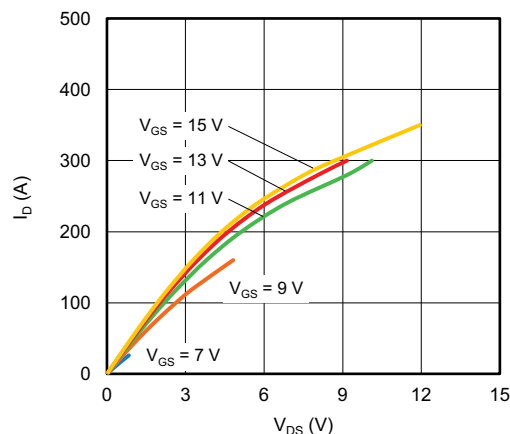
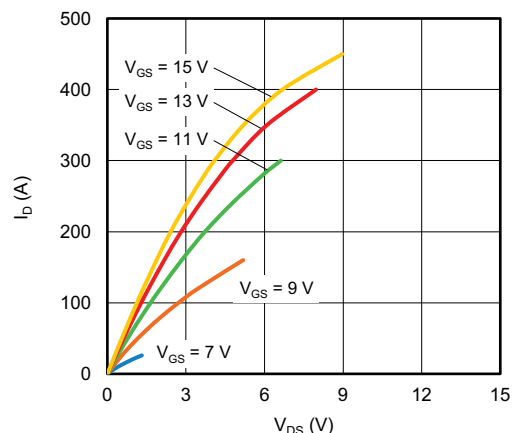
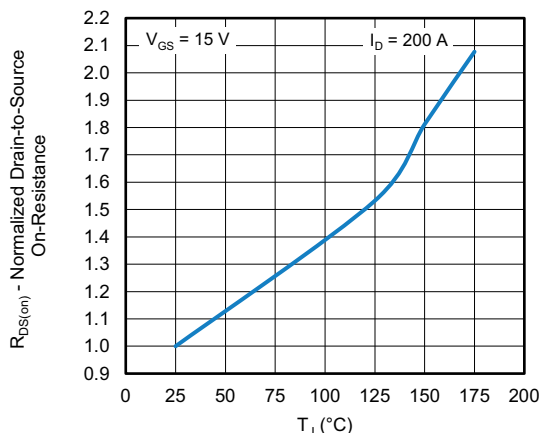

Fig. 3 - Typical Drain to Source Current Output Characteristics at $T_J = 150\text{ }^{\circ}\text{C}$

Fig. 2 - Typical Drain to Source Current Output Characteristics at $T_J = 25\text{ }^{\circ}\text{C}$


Fig. 4 - Normalized Drain-to-Source On-Resistance vs. Temperature

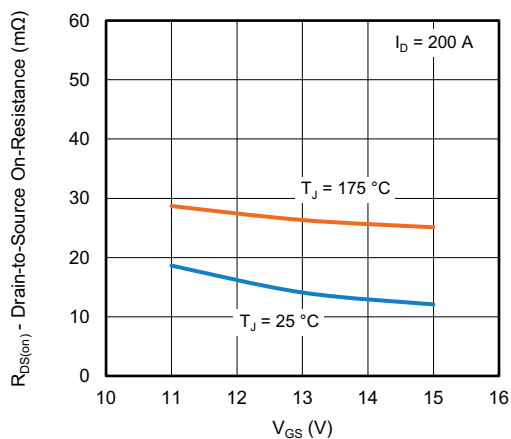


Fig. 5 - Typical Drain-to-Source On-Resistance vs. Gate to Source Voltage

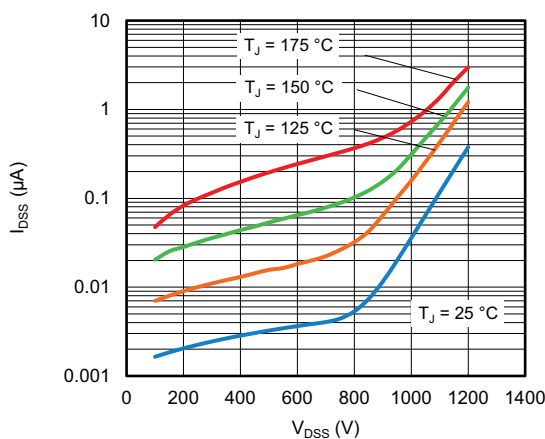


Fig. 8 - Typical Zero Gate Voltage Drain Current

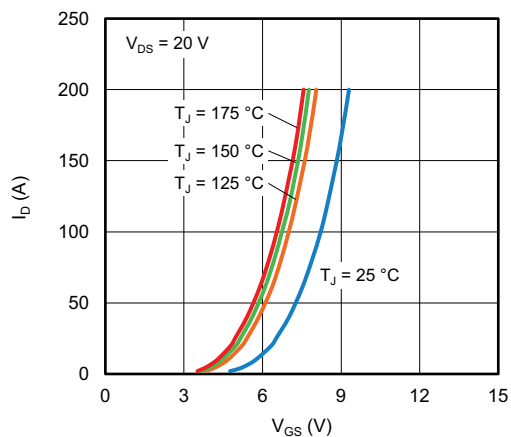


Fig. 6 - Typical Transfer Characteristics

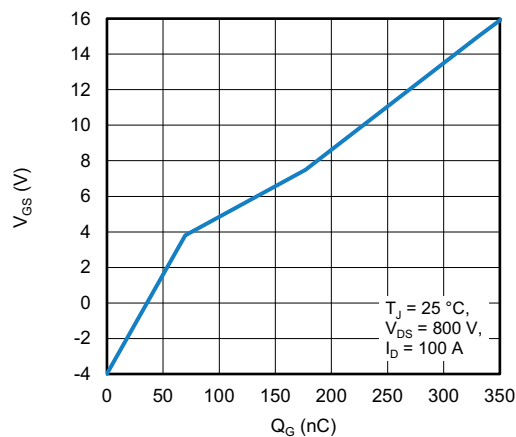


Fig. 9 - Typical Gate Charge vs. Gate to Source Voltage

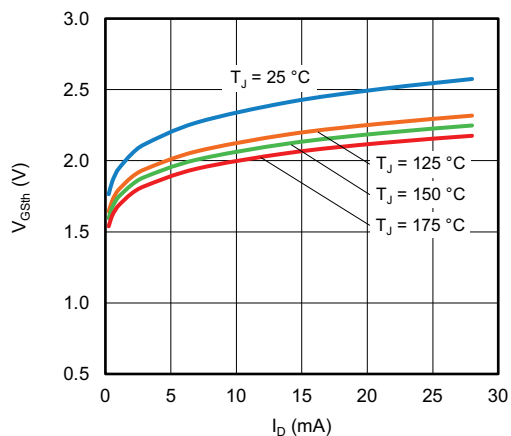


Fig. 7 - Typical Gate Threshold Voltage Characteristics

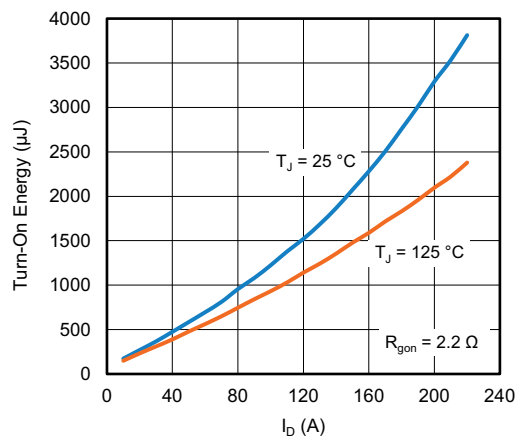
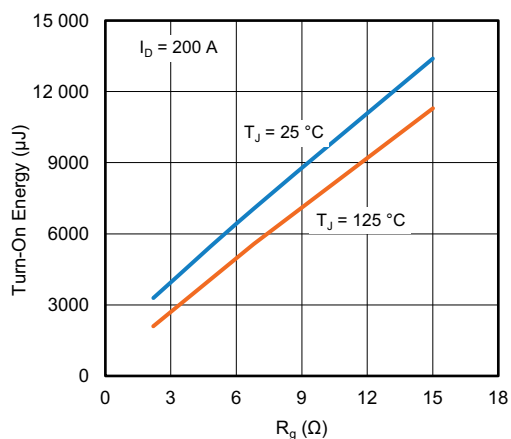
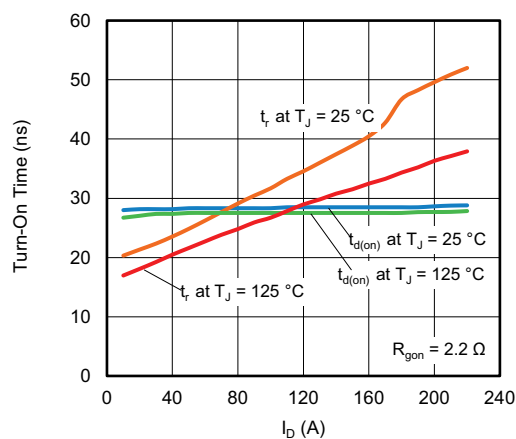
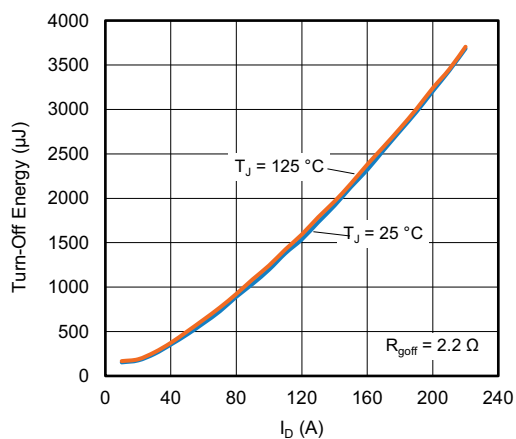
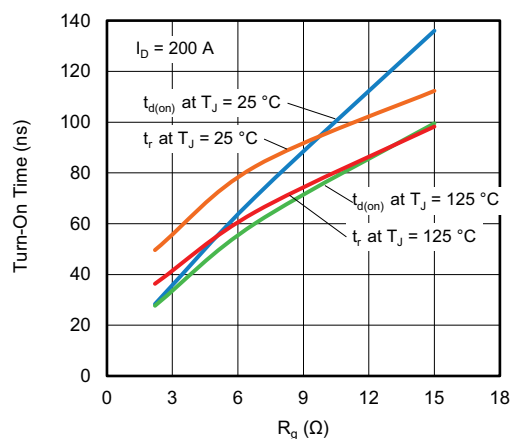
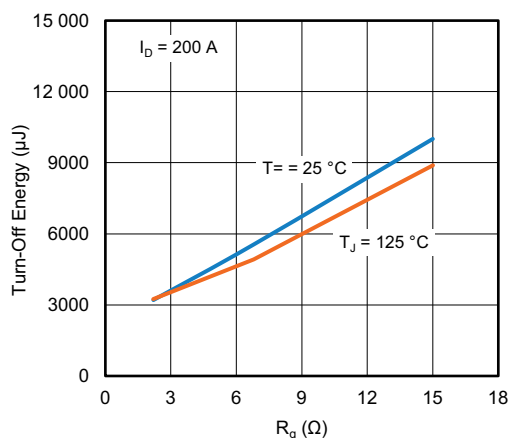
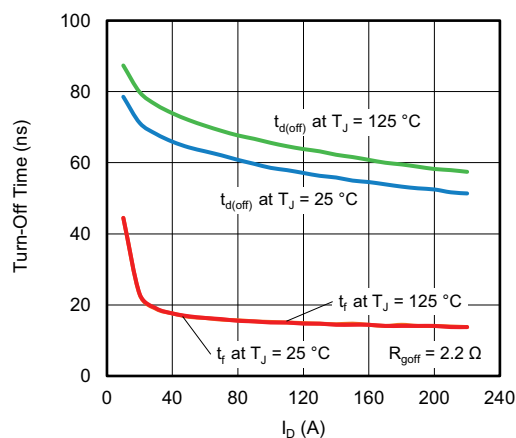


Fig. 10 - Typical Turn-On Energy Loss vs. I_D


Fig. 11 - Typical Turn-On Energy Loss vs. R_g

Fig. 14 - Typical Turn-On Switching Time vs. I_D

Fig. 12 - Typical Turn-Off Energy Loss vs. I_D

Fig. 15 - Typical Turn-On Switching Time vs. R_g

Fig. 13 - Typical Turn-Off Energy Loss vs. R_g

Fig. 16 - Typical Turn-Off Switching Time vs. I_D

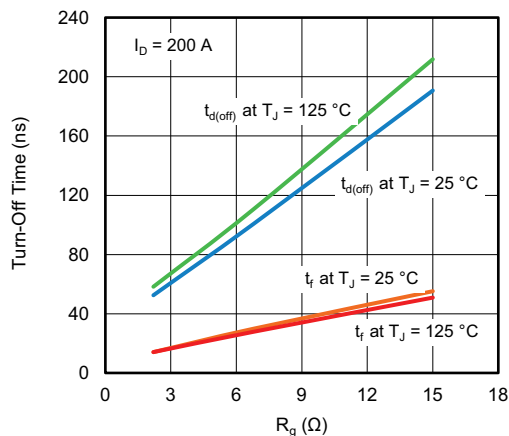
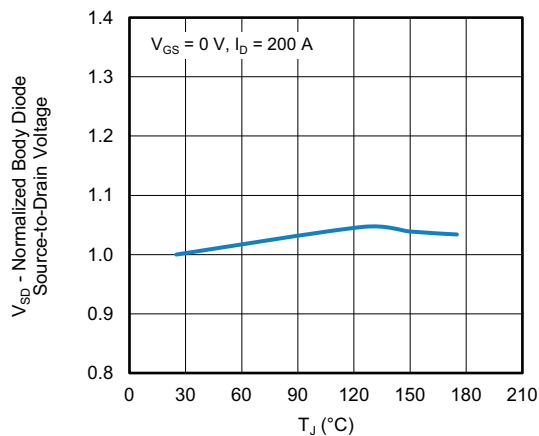

Fig. 17 - Typical Turn-Off Switching Time vs. R_g


Fig. 20 - Normalized Body Diode Source-to-Drain vs. Temperature

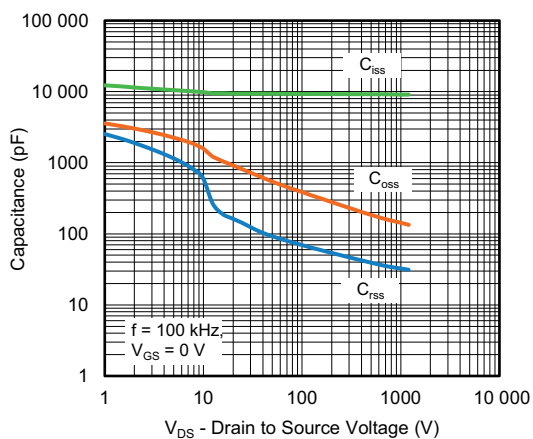


Fig. 18 - Capacitance vs. Drain-to-Source Voltage

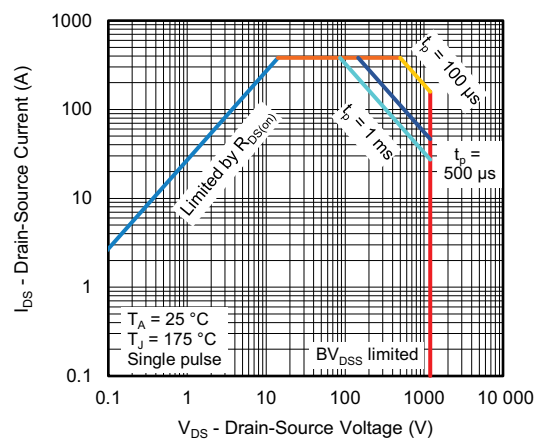


Fig. 21 - Safe Operating Area

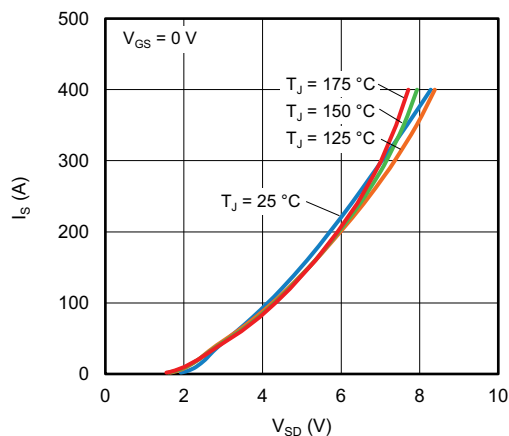


Fig. 19 - Typical Body Diode Source-to-Drain Current Characteristics

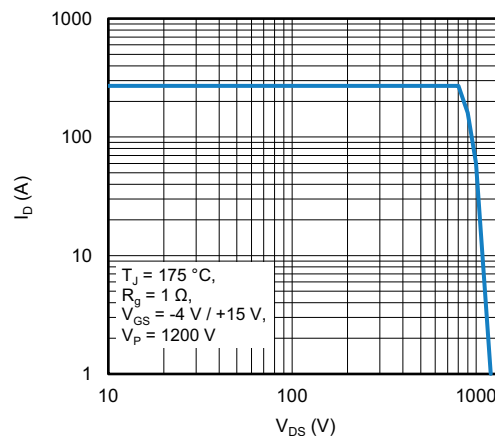


Fig. 22 - Reverse BIAS Safe Operating Area

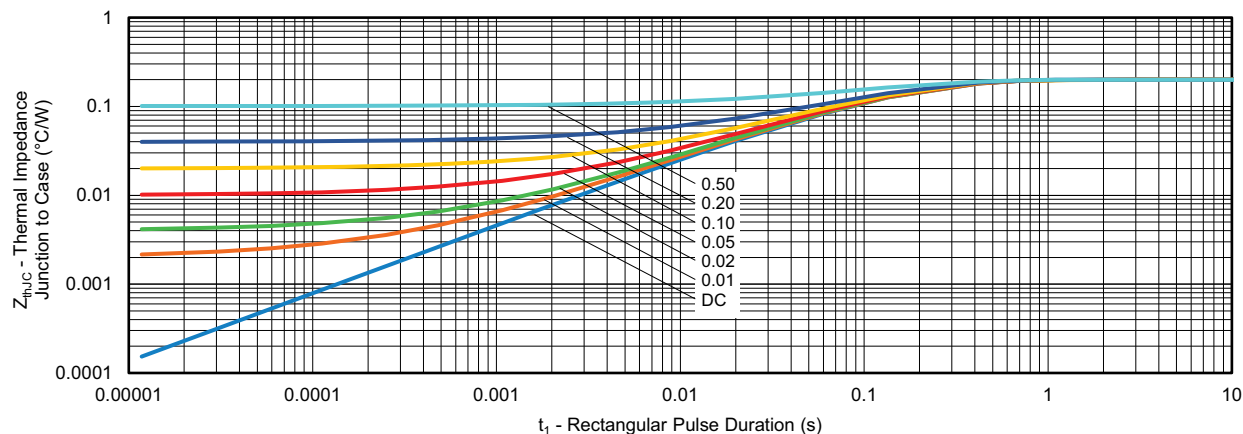


Fig. 23 - Maximum Thermal Impedance Z_{thJC} Characteristics

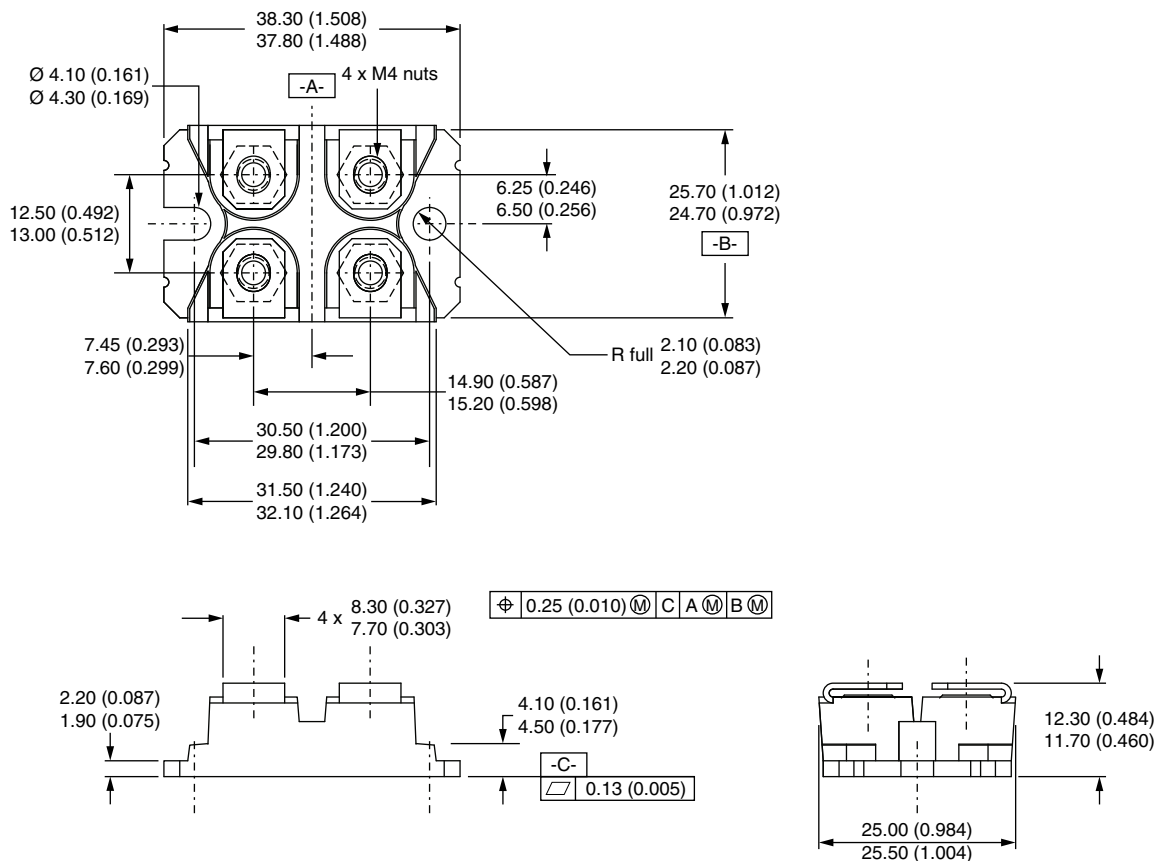
ORDERING INFORMATION TABLE

Device code	VS-	SF	200	S	A	120
	①	②	③	④	⑤	⑥
①	- Vishay Semiconductors product					
②	- SF = SiC MOSFET module					
③	- Current rating (200 = 200 A)					
④	- Circuit configuration (S = single switch)					
⑤	- Package indicator (SOT-227)					
⑥	- Voltage rating (120 = 1200 V)					

CIRCUIT CONFIGURATION		
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Single switch	S	

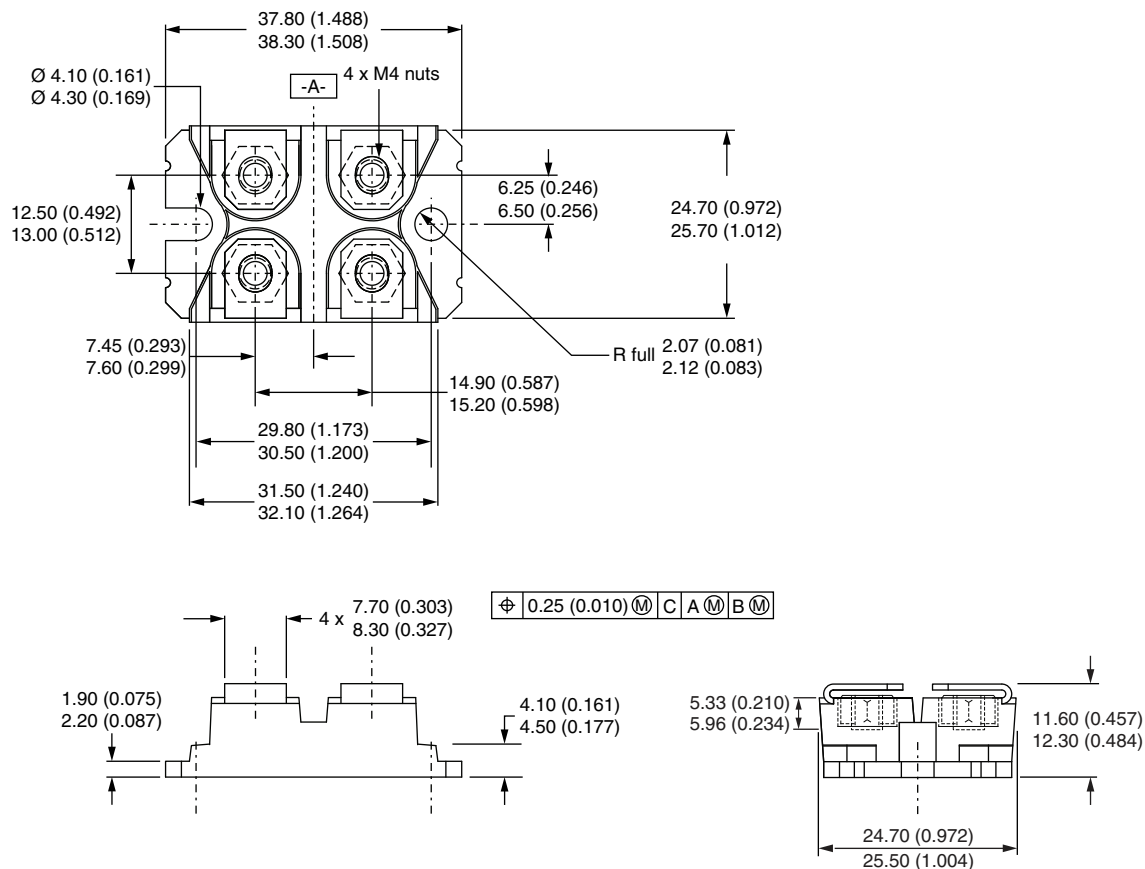


DIMENSIONS in millimeters



SOT-227 Generation 2

DIMENSIONS in millimeters (inches)



Note

- Controlling dimension: millimeter



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